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Phase diagrams of novel Tl₄SnSe₄—TlSbSe₂—Tl₂SnSe₃ quasi-ternary system following DTA and X-ray diffraction



I.E. Barchiy ^a, A.R. Tatzkar ^a, A.O. Fedorchuk ^b, K. Plucinski ^{c,*}

- ^a Department of Chemistry, Uzhgorod National University, Pidgirna St., 46, Uzhgorod 88000, Ukraine
- b Department of Inorganic and Organic Chemistry, Lviv National University of Veterinary Medicine and Biotechnologies, Pekarska St., 50, Lviv 79010, Ilkraine
- ^c Electronics Department, Military University Technology, Warsaw, Kaliskiego 2, Warsaw 00-908, Poland

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ABSTRACT

Phase relation in the Tl₄SnSe₄—TlSbSe₂—Tl₂SnSe₃ quasiternary system were studied by the DTA and X-ray diffraction in combination with mathematical modeling. The phase diagrams of the Tl₄SnSe₄—TlSbSe₂ and Tl₂SnSe₃—TlSbSe₂ systems, the perspective views of the phase interaction in the ternary system, the liquidus surface projection, the isothermal section at 423 K were built for the first time. The Tl₄SnSe₄—TlSbSe₂—Tl₂SnSe₃ system is of the invariant eutectic type and is characterized by the formation of limited solid solutions following initial ternary compounds. New complex compounds are not formed.

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1. Introduction

The one of the main tasks for the semiconductor materials science and engineering consists the development of new functional materials. Particular interest present complex Tl chalcogenide crystals and their alloy derivatives. Among them particular interest is attracted to the Tl₂Se–SnSe₂–Sb₂Se₃ ternary system. These ternary system are interesting for investigation due to formation of ternary compounds which reveal unusual optical, thermoelectric and photoelectrical behaviors. They have broad practical application in infrared optoelectronics, thermoelectricity, spirometry, optical triggering, gratings etc. Tl-containing structures are expected to possess low thermal conductivity due to effective scattering of phonons that are responsible for the transfer of heat in the materials. Thallium complex compounds have recently attracted interest as promising thermoelectric materials [1,2]. Thallium is similar in crystal chemical behavior to some of the alkali metals. It forms

preferentially compounds in oxidation state +1 and its ionic radius is very close to the ionic radius of potassium, however the electronegativity is higher. Replacement of potassium by thallium may enhance the electrical conductivity of a compound, as a result of substantial reduction of the ionicity of the chemical bonds. Also, thallium is a heavy element and its introduction into a semiconductor will lead to a decrease of the thermal conductivity.

The Tl₂Se-SnSe₂ system is characterized by the formations of Tl₄SnSe₄, Tl₂SnSe₃ ternary compounds, which congruently melt at 718 K and 738 K [3–6], respectively. In the Tl₂Se–Sb₂Se₃ system there are formed two congruently melting compounds: Tl₉SbSe₆ (743 K) and $TISb_2Se_2$ (730 K) [7–9]. The $SnSe_2-Sb_2Se_3$ system is of the eutectic type [10]. The Tl₂Se-SnSe₂-Sb₂Se₃ ternary system is divided into the five separate secondary subsystems Tl₂Se-Tl₄Sn-Tl₄SnSe₄-TlSbSe₂-Tl₉SbSe₆, Se₄–Tl₉SbSe₆, Tl₂SnSe₃—Tl₄Sn-Se₄-TlSbSe₂, Tl₂SnSe₃-TlSbSe₂-SnSe₂, SnSe₂-TlSbSe₂-Sb₂Se₃ with the four quasi-binary sections Tl₄SnSe₄-Tl₉SbSe₆, Tl₄SnSe₄-TlSbSe₂, Tl₂SnSe₃-TlSbSe₂ and SnSe₂-TlSbSe₂ [11,12]. The knowledge of the structure plays a crucial role for the design of crystals with advanced optoelectronic features [12-17] including infrared photo-transparency, multi-photon excitation, optical

^{*} Corresponding author. E-mail address: kpluc2006@wp.pl (K. Plucinski).

modulators in the Ir spectral range. In the present work we will present the data of the DTA and X-ray diffraction studies in combination with mathematical modeling of the phase diagrams for the Tl_4SnSe_4 — $TlSbSe_2$ and Tl_2SnSe_3 — $TlSbSe_2$ systems. Furthermore, the perspective views of the phase interaction in the ternary system, the liquidus surface projection, the isothermal section will be explored.

2. Materials and methods

As educts we used thallium (I), tin (IV) and stibium (III) selenides. Synthesis of these binary compounds was carried out with high-purity elements (better than 99.99 wt.%). T1₂Se, SnSe₂ and Sb₂Se₃ binary compounds were prepared by the single-temperature method from stoichiometric amounts of the initial elements in evacuated quartz containers. The binary compounds were purified by zone crystallization methods. The Tl₄SnSe₄, Tl₂SnSe₃ and TlSbSe₂ ternary compounds were obtained from stoichiometric amounts of initial binary selenides. Identification of binary and ternary compounds was done by the DTA and X-ray analysis.

The multicomponent alloys were synthesized from ternary complex selenides in quartz ampoules evacuated to a residual pressure of 0.13 Pa. After thermal treatment at highest temperature (823 K) for 24 h the samples were slowly cooled (25–30 K per hour) down to 423 K and homogenized at this temperature for 336 h. Subsequently the ampoules were quenched into cold water.

The phase equilibria in the ternary system were investigated by the differential thermal (DTA), X-ray powder diffraction, microstructure (MSA) analyses. More details about the performed DTA, XRD diffraction and microstructure are given in the Supplement 1. The classical methods of physico-chemical analysis were used in combination with the simplex method of mathematical modeling of phase equilibria in multicomponent systems [18]. More details about this modeling approach are given in the Supplement 2. The differential thermal analysis was carried out by means of a device including an x-y recorder PDA-1 and a chromelalumel thermocouple, with an accuracy of ±5 K. The samples were heated and cooled in a furnace using an RIF-101 programmer, which provided a linear temperature variation. X-ray powder diffraction was carried out on a DRON-3-13 diffractometer (Cu Kα radiation, Ni filter). Rietveld refinements of X-ray powder diffraction data were performed by using the WinCSD program [19]. The microstructure analysis was carried out with a metallographic microscope Lomo Metam R1.

3. Results and discussion

3.1. Tl₄SnSe₄—TlSbSe₂ quasibinary system

Tl₄SnSe₄—TlSbSe₂ quasibinary system is characterized by the eutectic processes L \leftrightarrow Tl₄SnSe₄ + htmTlSbSe₂ (see Fig.1). The lines of primary crystallization are intersected in the invariant point with coordinates 62 mol./% TlSbSe₂, 619K. Limited solid solutions are formed in the system: β on the base of Tl₄SnSe₄ and δ , δ' following low-, high-temperature polymorphic modification of TlSbSe₂, respectively. Eutectical processes $\delta' \leftrightarrow \beta + \delta$ is observed at 595 K. The solid solution range based on TlSbSe₂ do not exceed 14 mol.% at 423 K.

3.2. Tl₂SnSe₃-TlSbSe₂ quasibinary system

The phase diagram of the Tl_2SnSe_3 — $TlSbSe_2$ system is presented in Fig.2. This system belongs to the Rozeboom type V and is

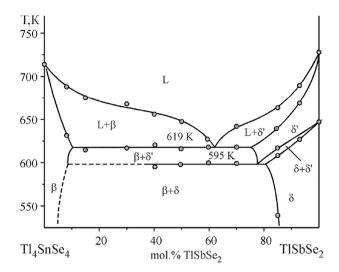


Fig. 1. Phase diagram of the Tl_4SnSe_4 – $TlSbSe_2$ system (the accuracy of the points corresponds to 5 K).

characterized bv the invariant eutectic processes $L \leftrightarrow ltmTl_2SnSe_3 + htmTlSbSe_2$. The coordinates of the eutectic point correspond to 70 mol.% TISbSe2 at 635K. In this system are formed ε , ε' solid solutions based on low-, high-temperature polymorphic modifications of Tl_2SnSe_3 and δ , δ' solid solutions based on low-, high-temperature polymorphic modifications of TISbSe₂, respectively. The metatectic processes $\varepsilon' \leftrightarrow L + \varepsilon$ based on the polymorphic transformation of the ternary compound Tl₂SnSe₃ is observed at 693 K, eutectic processes $\delta' \leftrightarrow \varepsilon + \delta$ based on the polymorphic transformation of TISbSe₂ takes place at 597 K. At 423 K the existence of the solid solution range of low-temperature polymorphic modification of TISbSe₂ is less than 11 mol.%. The lattice parameters of initial ternary compounds and solid solutions based on TISbSe2 are shown in Table 1.

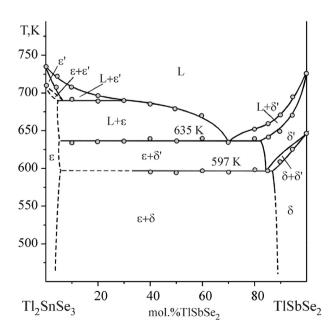


Fig. 2. Phase diagram of the Tl_2SnSe_3 — $TlSbSe_2$ system (the accuracy of the points corresponds to 5 K).

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